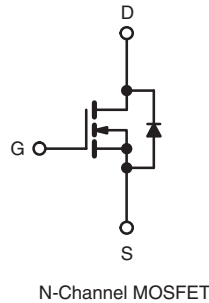
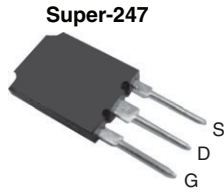


## Power MOSFET



### FEATURES

- Superfast body diode eliminates the need for External diodes in ZVS applications
- Lower gate charge results in simpler drive requirements
- Enhanced dV/dt capabilities offer improved ruggedness
- Higher gate voltage threshold offers improved noise immunity
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



### APPLICATIONS

- Zero voltage switching SMPS
- Telecom and server power supplies
- Uninterruptible power supplies
- Motor control applications

PRODUCT SUMMARY	
$V_{DS}$ (V)	500
$R_{DS(on)}$ ( $\Omega$ )	$V_{GS} = 10\text{ V}$ 0.087
$Q_g$ (Max.) (nC)	380
$Q_{gs}$ (nC)	80
$Q_{gd}$ (nC)	190
Configuration	Single

ORDERING INFORMATION	
Package	Super-247
Lead (Pb)-free and halogen free	SiHFPS40N50L-GE3

ABSOLUTE MAXIMUM RATINGS ( $T_C = 25\text{ }^\circ\text{C}$ , unless otherwise noted)				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-source voltage	$V_{DS}$	500	V	
Gate-source voltage	$V_{GS}$	$\pm 30$		
Continuous drain current	$V_{GS}$ at 10 V	$T_C = 25\text{ }^\circ\text{C}$	46	
		$T_C = 100\text{ }^\circ\text{C}$	29	
Pulsed drain current <sup>a</sup>	$I_{DM}$	180	A	
Linear derating factor		4.3	W/ $^\circ\text{C}$	
Single pulse avalanche energy <sup>b</sup>	$E_{AS}$	920	mJ	
Repetitive avalanche current <sup>a</sup>	$I_{AR}$	46	A	
Repetitive avalanche Energy <sup>a</sup>	$E_{AR}$	54	mJ	
Maximum power dissipation	$T_C = 25\text{ }^\circ\text{C}$	$P_D$	540	W
Peak diode recovery dV/dt <sup>c</sup>		dV/dt	34	V/ns
Operating junction and storage temperature range	$T_J, T_{stg}$	- 55 to + 150	$^\circ\text{C}$	
Soldering recommendations (peak temperature)	for 10 s	300 <sup>d</sup>		

#### Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- Starting  $T_J = 25\text{ }^\circ\text{C}$ ,  $L = 0.86\text{ mH}$ ,  $R_g = 25\text{ }\Omega$ ,  $I_{AS} = 46\text{ A}$  (see fig. 12)
- $I_{SD} \leq 46\text{ A}$ ,  $dI/dt \leq 550\text{ A}/\mu\text{s}$ ,  $V_{DD} \leq V_{DS}$ ,  $T_J \leq 150\text{ }^\circ\text{C}$
- 1.6 mm from case




THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient <sup>a</sup>	R <sub>thJA</sub>	-	40	°C/W
Case-to-sink, flat, greased surface	R <sub>thCS</sub>	0.24	-	
Maximum junction-to-case (drain) <sup>a</sup>	R <sub>thJC</sub>	-	0.23	

**Note**

a. R<sub>th</sub> is measured at T<sub>J</sub> approximately 90 °C

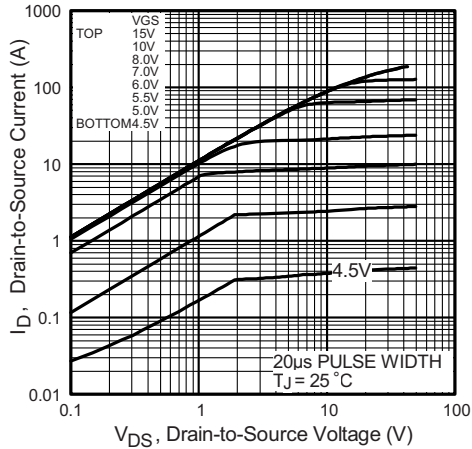
**SPECIFICATIONS** (T<sub>J</sub> = 25 °C, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-source breakdown voltage	V <sub>DS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	500	-	-	V
V <sub>DS</sub> temperature coefficient	ΔV <sub>DS</sub> /T <sub>J</sub>	Reference to 25 °C, I <sub>D</sub> = 1 mA	-	0.60	-	V/°C
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	3.0	-	5.0	V
Gate-source leakage	I <sub>GSS</sub>	V <sub>GS</sub> = ± 30 V	-	-	± 100	nA
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = 500 V, V <sub>GS</sub> = 0 V	-	-	50	μA
		V <sub>DS</sub> = 400 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C	-	-	2.0	mA
Drain-source on-state resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 28 A <sup>b</sup>	-	0.087	0.100	Ω
Forward transconductance	g <sub>fs</sub>	V <sub>DS</sub> = 50 V, I <sub>D</sub> = 46 A	21	-	-	S
<b>Dynamic</b>						
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 25 V, f = 1.0 MHz, see fig. 5	-	8110	-	pF
Output capacitance	C <sub>oss</sub>		-	960	-	
Reverse transfer capacitance	C <sub>rss</sub>		-	130	-	
Output capacitance	C <sub>oss</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 1.0 V, f = 1.0 MHz	-	11200	-
			V <sub>DS</sub> = 400 V, f = 1.0 MHz	-	240	-
Effective output capacitance	C <sub>oss eff.</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 0 V to 400 V <sup>c</sup>	-	440	-
Effective output capacitance (energy related)	C <sub>oss eff. (ER)</sub>			-	310	-
Total gate charge	Q <sub>g</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 46 A, V <sub>DS</sub> = 400 V, see fig. 7 and 15 <sup>b</sup>	-	-	380
Gate-source charge	Q <sub>gs</sub>			-	-	80
Gate-drain charge	Q <sub>gd</sub>			-	-	190
Internal gate resistance	R <sub>g</sub>	f = 1 MHz, open drain		-	0.90	-
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> = 250 V, I <sub>D</sub> = 46 A, R <sub>g</sub> = 0.85 Ω, V <sub>GS</sub> = 10 V, see fig. 14a and 14b <sup>b</sup>	-	27	-	ns
Rise time	t <sub>r</sub>		-	170	-	
Turn-off delay time	t <sub>d(off)</sub>		-	50	-	
Fall time	t <sub>f</sub>		-	69	-	
<b>Drain-source body diode characteristics</b>						
Continuous source-drain diode current	I <sub>S</sub>	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	46	A
Pulsed diode forward current <sup>a</sup>	I <sub>SM</sub>		-	-	180	
Body diode voltage	V <sub>SD</sub>	T <sub>J</sub> = 25 °C, I <sub>S</sub> = 46 A, V <sub>GS</sub> = 0 V <sup>b</sup>	-	-	1.5	V
Body diode reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C, I <sub>F</sub> = 46 A	-	170	250	ns
		T <sub>J</sub> = 125 °C, dI/dt = 100 A/μs <sup>b</sup>	-	220	330	
Body diode reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 25 °C, I <sub>S</sub> = 46 A, V <sub>GS</sub> = 0 V <sup>b</sup>	-	705	1060	nC
		T <sub>J</sub> = 125 °C, dI/dt = 100 A/μs <sup>b</sup>	-	1.3	2.0	
Reverse recovery current	I <sub>RRM</sub>	T <sub>J</sub> = 25 °C	-	9.0	-	A
Forward turn-on time	t <sub>on</sub>	Intrinsic turn-on time is negligible (turn-on is dominated by L <sub>S</sub> and L <sub>D</sub> )				

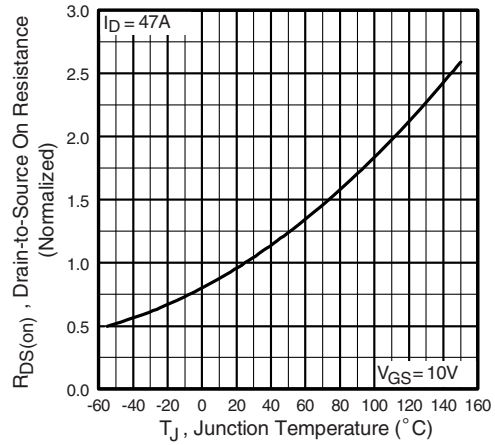
**Notes**

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- b. Pulse width ≤ 400 μs; duty cycle ≤ 2 %
- c. C<sub>oss eff.</sub> is a fixed capacitance that gives the same charging time as C<sub>oss</sub> while V<sub>DS</sub> is rising from 0 % to 80 % V<sub>DS</sub>  
C<sub>oss eff. (ER)</sub> is a fixed capacitance that stores the same energy as C<sub>oss</sub> while V<sub>DS</sub> is rising from 0 % to 80 % V<sub>DS</sub>

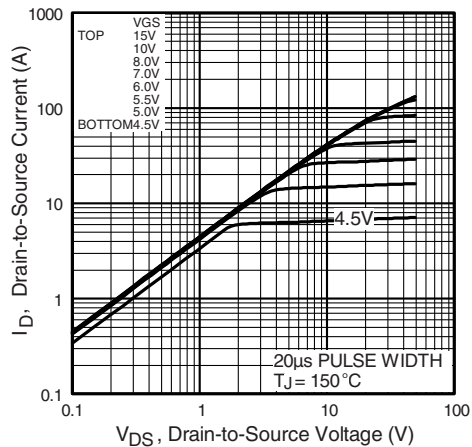
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



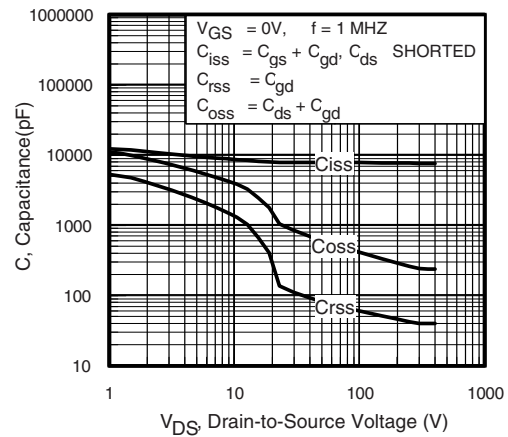
**Fig. 1 - Typical Output Characteristics**



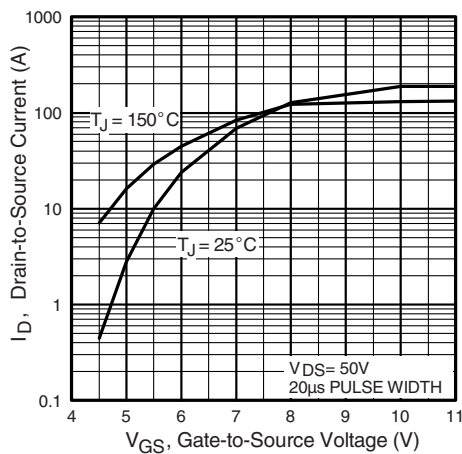
**Fig. 4 - Normalized On-Resistance vs. Temperature**



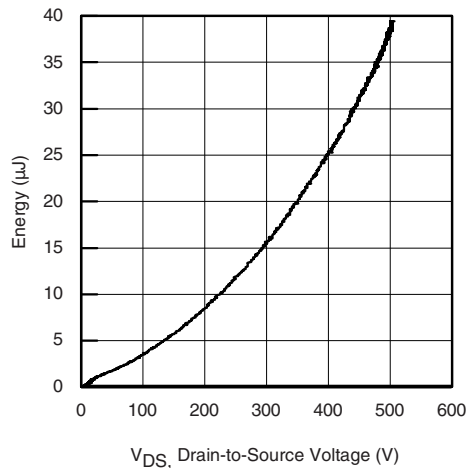
**Fig. 2 - Typical Output Characteristics**



**Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage**



**Fig. 3 - Typical Transfer Characteristics**



**Fig. 6 - Typical Output Capacitance Stored Energy vs. VDS**

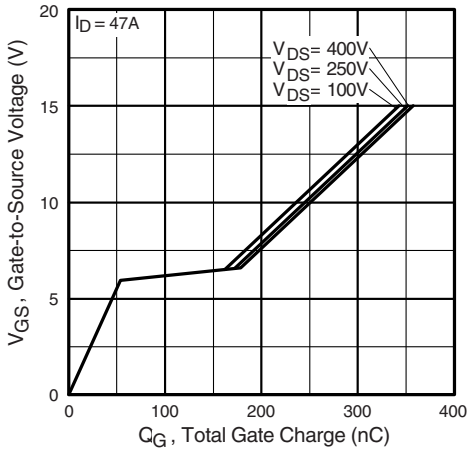


Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage

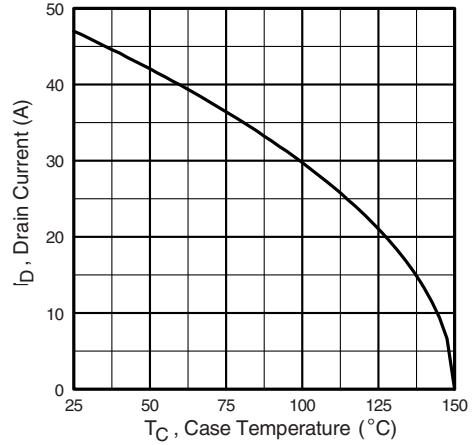


Fig. 9 - Maximum Drain Current vs. Case Temperature

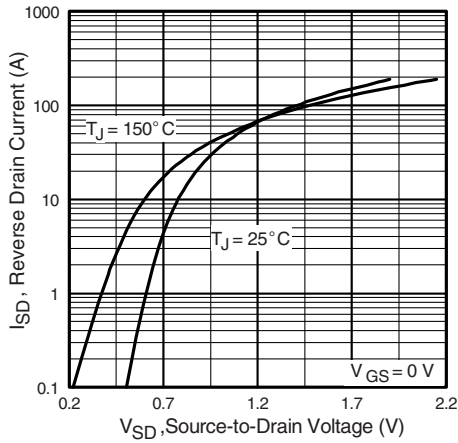


Fig. 8 - Typical Source Drain Diode Forward Voltage

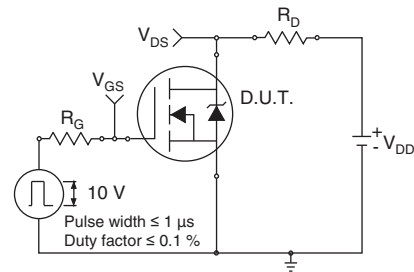


Fig. 10a - Switching Time Test Circuit

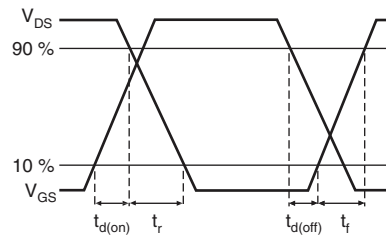


Fig. 10b - Switching Time Waveforms

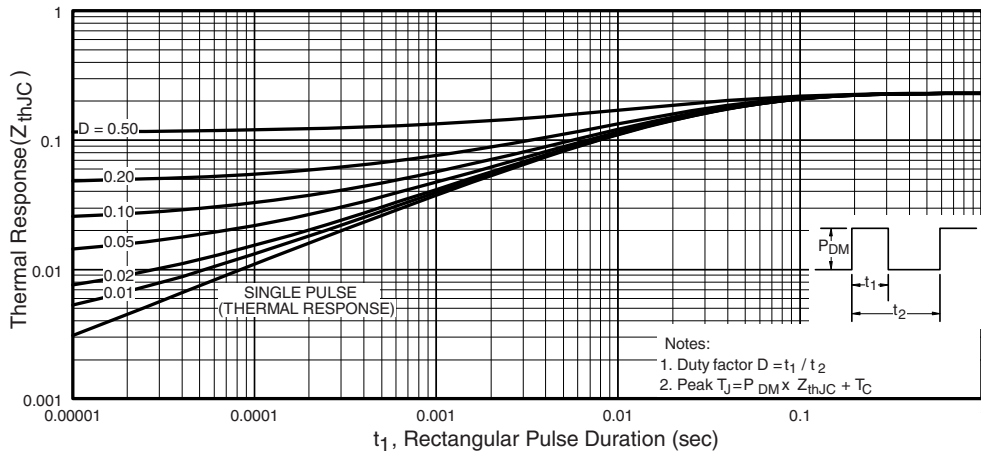


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

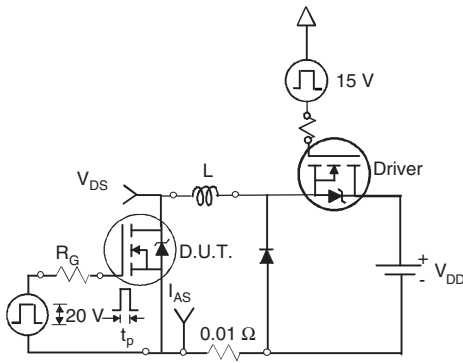


Fig. 12a - Unclamped Inductive Test Circuit

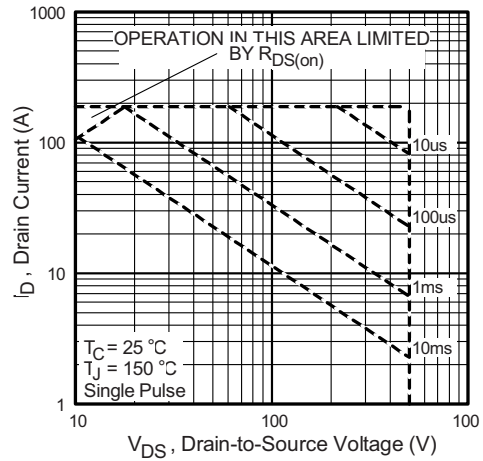


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

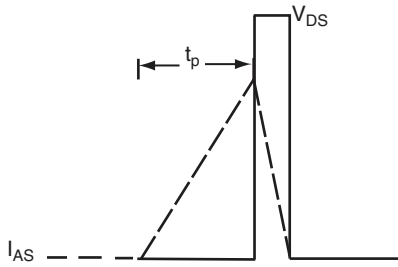


Fig. 12b - Unclamped Inductive Waveforms

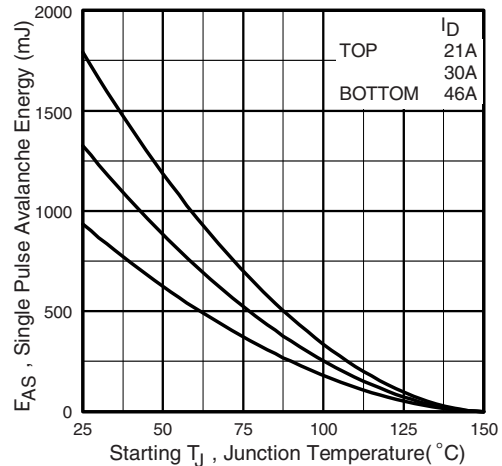


Fig. 12d - Maximum Safe Operating Area

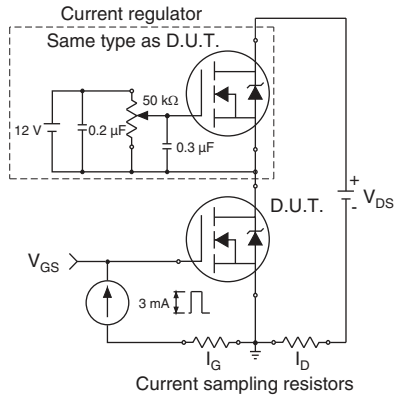


Fig. 13a - Gate Charge Test Circuit

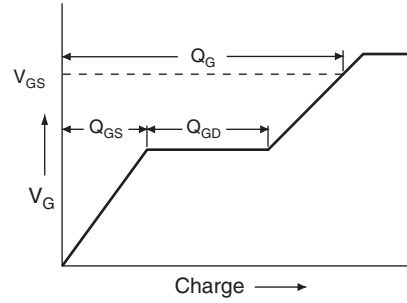
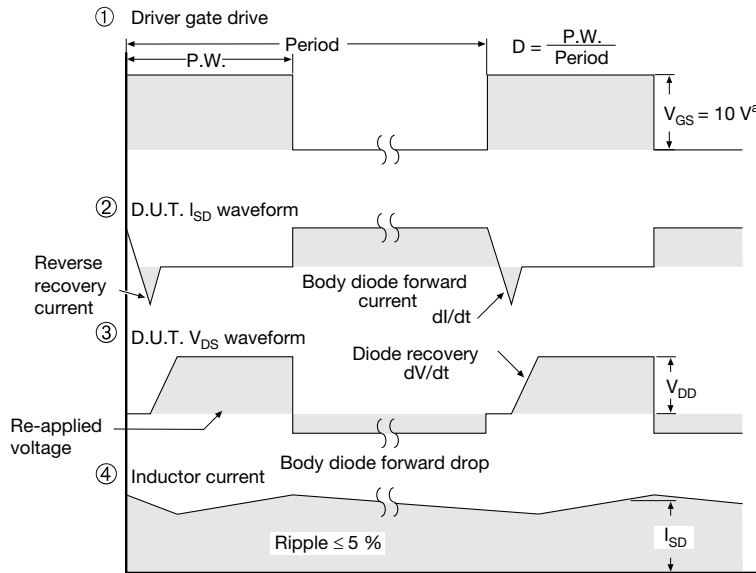
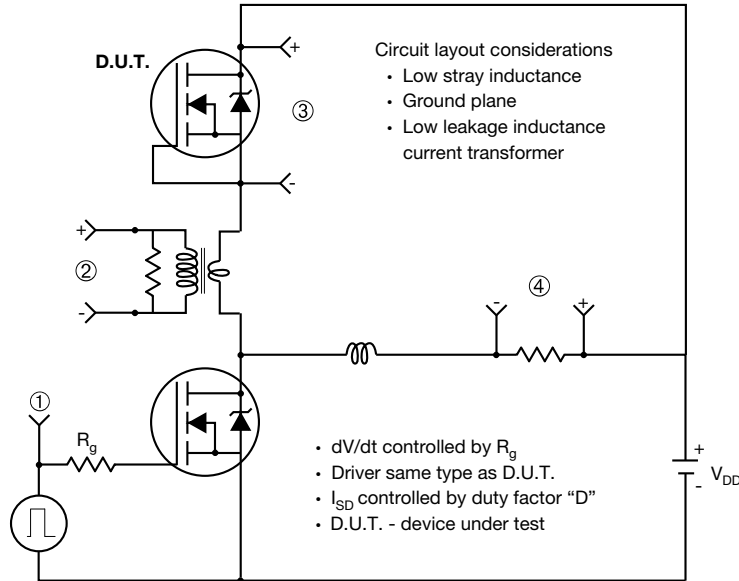


Fig. 13b - Basic Gate Charge Waveform

Peak Diode Recovery dV/dt Test Circuit



Note

a.  $V_{GS} = 5 V$  for logic level devices

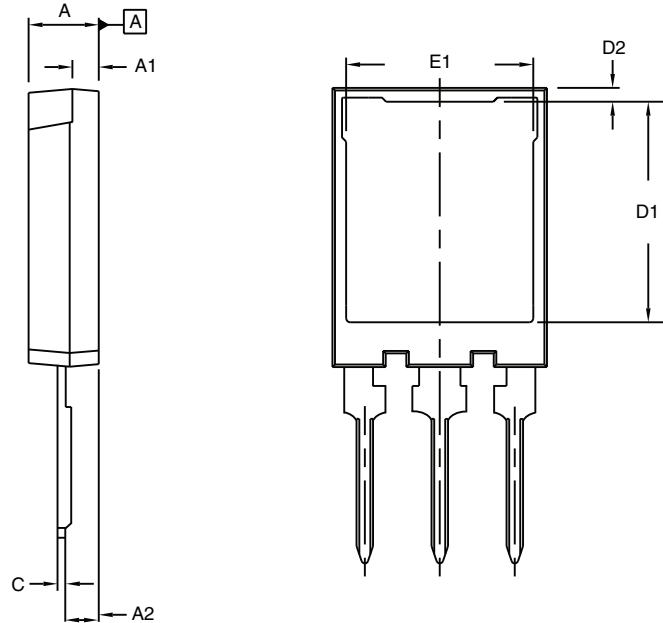
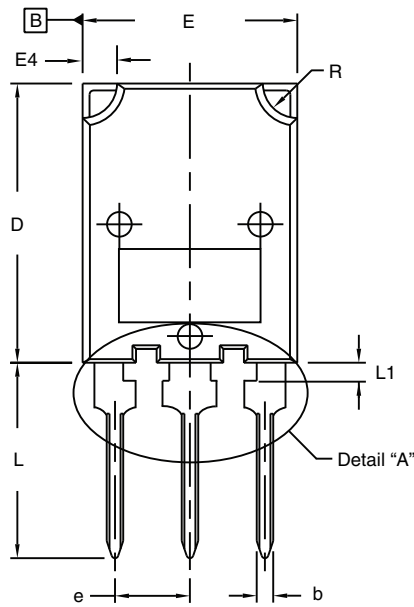
Fig. 14 - For N-Channel

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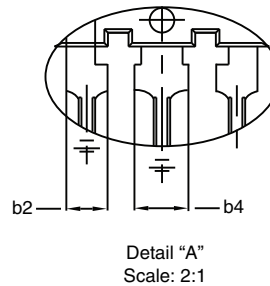
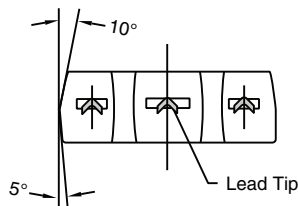


# TO-274AA (High Voltage)

## VERSION 1: FACILITY CODE = Y



⌀ 0.10 (0.25) Ⓜ B A Ⓜ



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.70	5.30	0.185	0.209
A1	1.50	2.50	0.059	0.098
A2	2.25	2.65	0.089	0.104
b	1.30	1.60	0.051	0.063
b2	1.80	2.20	0.071	0.087
b4	3.00	3.25	0.118	0.128
c <sup>(1)</sup>	0.38	0.89	0.015	0.035
D	19.80	20.80	0.780	0.819

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
D1	15.50	16.10	0.610	0.634
D2	0.70	1.30	0.028	0.051
E	15.10	16.10	0.594	0.634
E1	13.30	13.90	0.524	0.547
e	5.45 BSC		0.215 BSC	
L	13.70	14.70	0.539	0.579
L1	1.00	1.60	0.039	0.063
R	2.00	3.00	0.079	0.118

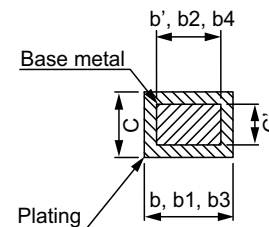
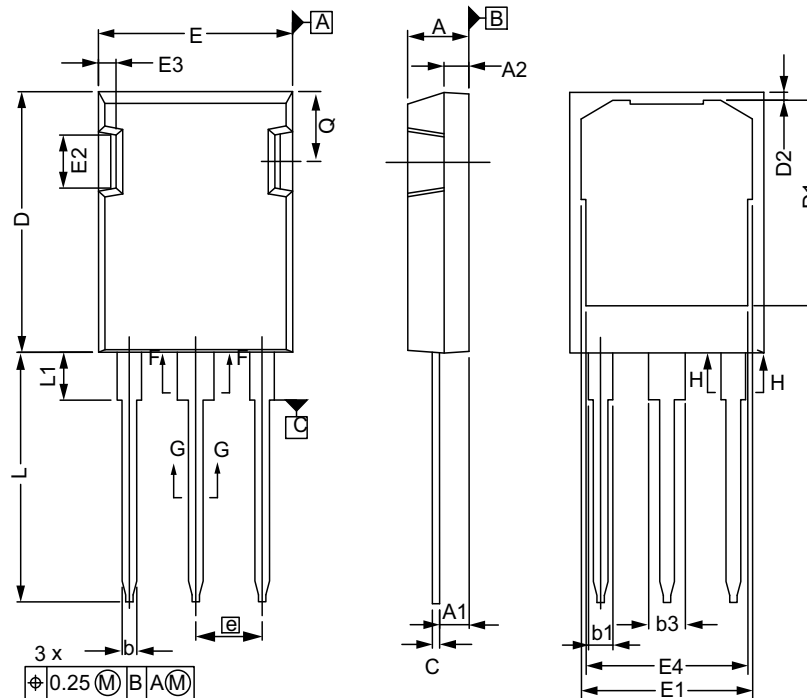
### Notes

- Dimensioning and tolerancing per ASME Y14.5M-1994
- Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outer extremes of the plastic body
- Outline conforms to JEDEC® outline to TO-274AA
- (1) Dimension measured at tip of lead





VERSION 2: FACILITY CODE = N



SECTION "F-F", "G-G" AND "H-H"  
SCALE: NONE

DIM.	MILLIMETERS	
	MIN.	MAX.
A	4.83	5.21
A1	2.29	2.54
A2	1.91	2.16
b'	1.07	1.28
b	1.07	1.33
b1	1.91	2.41
b2	1.91	2.16
b3	2.87	3.38
b4	2.87	3.13
c'	0.55	0.65
c	0.55	0.68
D	20.80	21.10

DIM.	MILLIMETERS	
	MIN.	MAX.
D1	16.25	17.65
D2	0.50	0.80
E	15.75	16.13
E1	13.10	14.15
E2	3.68	5.10
E3	1.00	1.90
E4	12.38	13.43
e	5.44 BSC	
N	3	
L	19.81	20.32
L1	3.70	4.00
Q	5.49	6.00

ECN: E20-0538-Rev. C, 19-Oct-2020  
DWG: 5975

Notes

- Dimensioning and tolerancing per ASME Y14.5M-1994
- Outline conforms to JEDEC® outline to TO-274AD
- Dimensions are measured in mm, angles are in degree
- Metal surfaces are tin plated, except area of cut



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